

| L Number | Hits | Search Text   | DB  | Time stamp          |
|----------|------|---|---|---------------------|
| 1        | 237  | plasma near2 (CVD or chemical near2 vapor near2 deposit\$5) same ion near2 beam same (si or silicon)                  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/10/12<br>11:10 |
| 3        | 19   | plasma near2 (CVD or chemical near2 vapor near2 deposit\$5) near10 ion near2 beam near10 (si or silicon)              | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/10/12<br>11:11 |
| 2        | 93   | plasma near2 (CVD or chemical near2 vapor near2 deposit\$5) near10 ion near2 beam same (si or silicon)                | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/10/12<br>11:13 |
| 4        | 93   | plasma near2 (CVD or chemical near2 vapor near2 deposit\$5) near10 (si or silicon) same (ion near2 beam)              | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/10/12<br>11:37 |
| 5        | 50   | (plasma near2 (CVD or chemical near2 vapor near2 deposit\$5) or PECVD) near10 (si or silicon) same ion near2 source   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/10/12<br>13:20 |
| 6        | 0    | 5795385.pn. and silane same (hydrogen or "h.sub.2")   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/10/12<br>13:21 |
| 7        | 1    | 5795385.pn. and (hydrogen or "h.sub.2")   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/10/12<br>13:21 |
| 8        | 592  | (kirimura near2 hiroya or kiyoshi near2 ogata).in.  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/10/12<br>13:24 |
| 9        | 26   | ((kirimura near2 hiroya or kiyoshi near2 ogata).in.) and (silicon or si) near2 (film or layer) same (laser)           | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/10/12<br>13:37 |
| 10       | 9    | ((kirimura near2 hiroya or kiyoshi near2 ogata).in.) and (silicon or si) near2 (film or layer) same energy near2 beam | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/10/12<br>13:37 |
| -        | 2    | laser same recrystal\$8 same (silicon or si) near10 crystal\$7 same deposit\$5 same in\$1situ                         | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/10/05<br>13:45 |
| -        | 4    | laser same recrystal\$8 same (silicon or si) near10 crystal\$7 same deposit\$5 same chamber                           | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/10/05<br>13:46 |
| -        | 15   | laser same recrystal\$8 same (silicon or si) same deposit\$5 same chamber   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/10/05<br>13:47 |
| -        | 2    | "20010032589"   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/10/05<br>14:07 |

|   |       |   |   |                     |
|---|-------|---|---|---------------------|
| - | 5     | "0652308"   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/10/05<br>13:52 |
| - | 9     | "652308"  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/10/05<br>13:56 |
| - | 41    | laser same deposit\$5 near10 (si or silicon) same in\$1situ   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/10/05<br>13:57 |
| - | 106   | single near5 (chamber or apparatus) same laser same deposit\$5  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/10/05<br>14:37 |
| - | 10087 | laser near5 (anneal\$5 or recrystal\$8)   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/10/05<br>14:37 |
| - | 4493  | ((laser near5 (anneal\$5 or recrystal\$8)) same (si or silicon) near5 (film or layer))  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/10/05<br>14:37 |
| - | 290   | ((laser near5 (anneal\$5 or recrystal\$8)) same (si or silicon) near5 (film or layer)) and vacuum near2 chamber               | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/10/05<br>14:38 |
| - | 24    | ((laser near5 (anneal\$5 or recrystal\$8)) same (si or silicon) near5 (film or layer)) same vacuum near2 chamber              | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/10/05<br>14:45 |
| - | 25    | ((laser near5 (anneal\$5 or recrystal\$8)) same (si or silicon) near5 (film or layer)) same (chamber or reactor) near5 "same" | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/10/05<br>15:01 |
| - | 43    | laser near5 (anneal\$5 or recrystal\$7) same (chamber or reactor) near5 "same"  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/10/05<br>15:06 |